

**SANYO**

No.3460

**2SK1457**

N-Channel MOS Silicon FET

Very High-Speed Switching Applications

**Features**

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

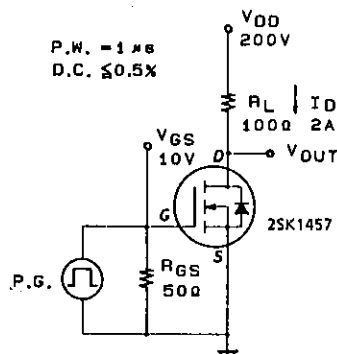
**Absolute Maximum Ratings at Ta=25°C**

			unit
Drain to Source Voltage	V <sub>DSS</sub>	900	V
Gate to Source Voltage	V <sub>GS</sub>	±30	V
Drain Current(DC)	I <sub>D</sub>	5	A
Drain Current(Pulse)	I <sub>DP</sub>	PW ≤ 10μs, duty cycle ≤ 1%	10
Allowable Power Dissipation	P <sub>D</sub>	Tc = 25°C	70
			1.75
Channel Temperature	T <sub>ch</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

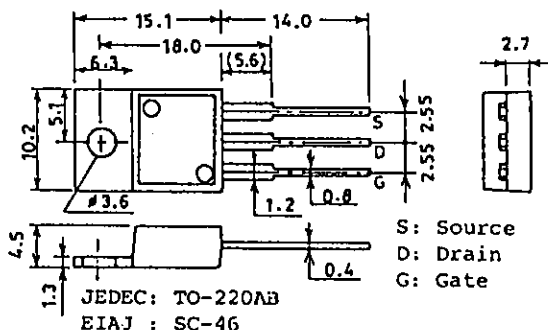
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 1mA, V <sub>GS</sub> = 0	900			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 900V, V <sub>GS</sub> = 0			1.0	mA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30V, V <sub>DS</sub> = 0			±100	nA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA	2.0		3.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 20V, I <sub>D</sub> = 2A	1.0	2.0		S
Static Drain to Source on State Resistance	R <sub>DS(on)</sub>	I <sub>D</sub> = 2A, V <sub>GS</sub> = 10V		2.8	3.6	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		700		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		300		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 20V, f = 1MHz		170		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	I <sub>D</sub> = 2A, V <sub>GS</sub> = 10V V <sub>DD</sub> = 200V, R <sub>GS</sub> = 50Ω		15		ns
Rise Time	t <sub>r</sub>		35	ns		
Turn-OFF Delay Time	t <sub>d(off)</sub>		200	ns		
Fall Time	t <sub>f</sub>		65	ns		
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 5A, V <sub>GS</sub> = 0			1.8	V

(Note) Be careful in handling the 2SK1457 because it has no protection diode between gate and source.

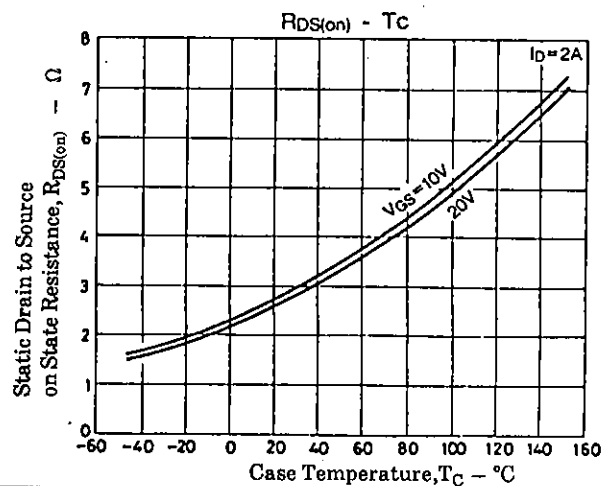
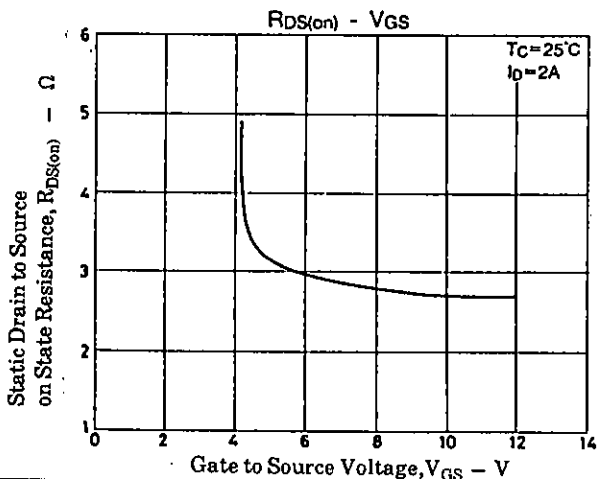
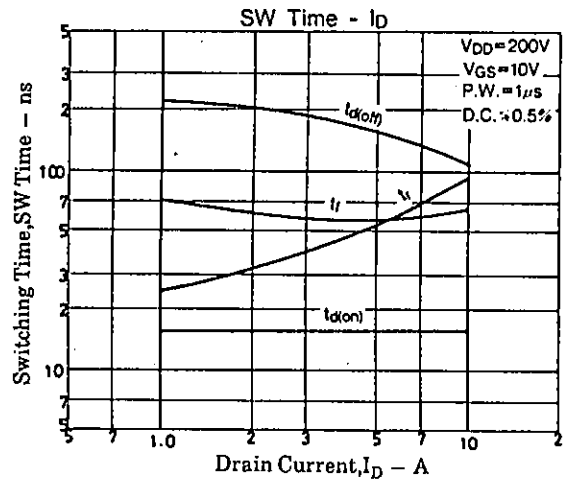
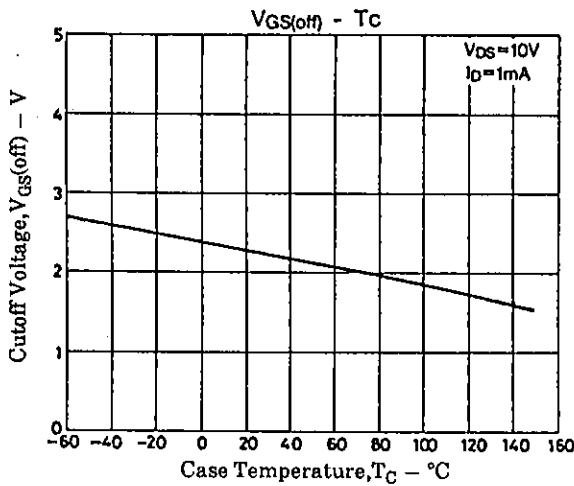
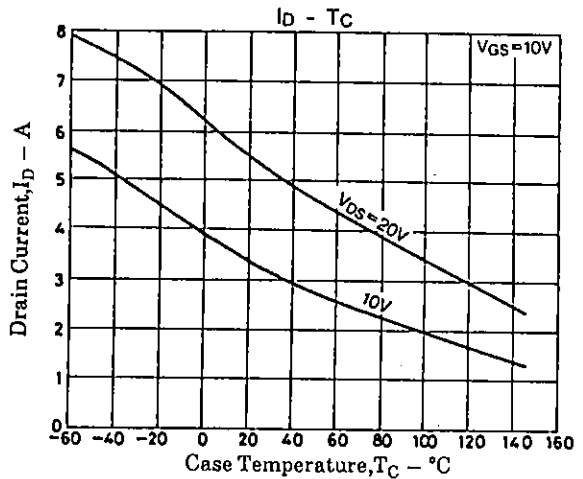
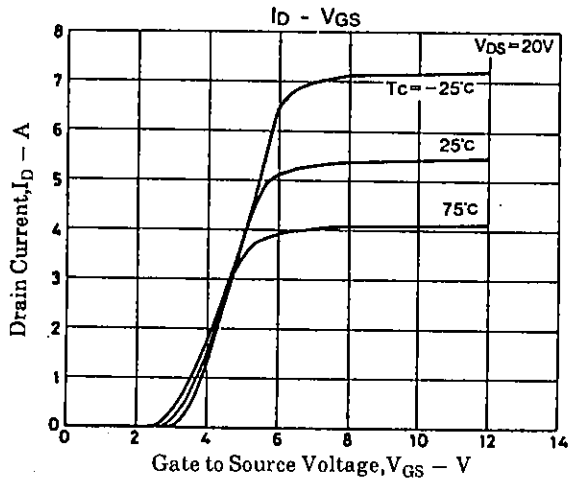
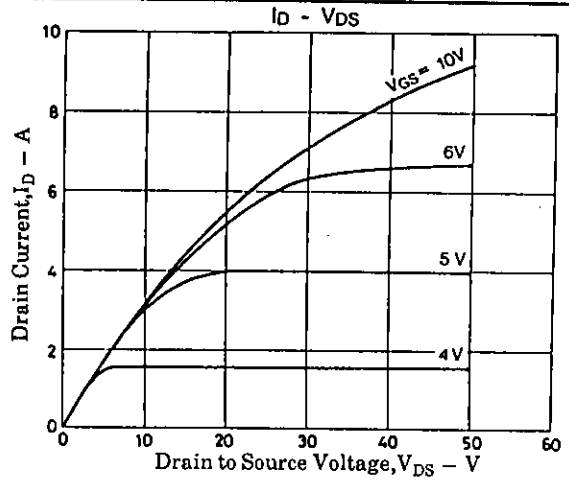
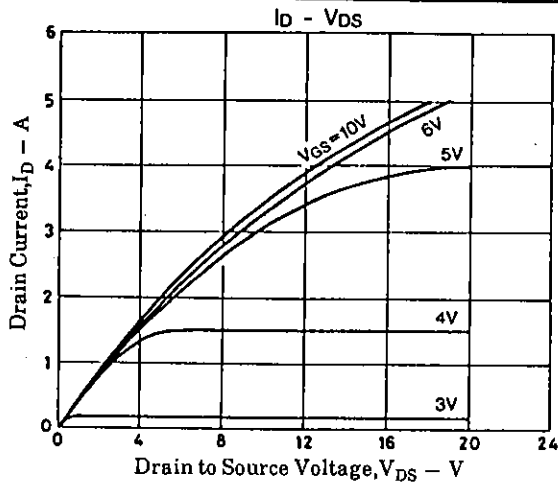
**Switching Time Test Circuit****Package Dimensions 2052B**

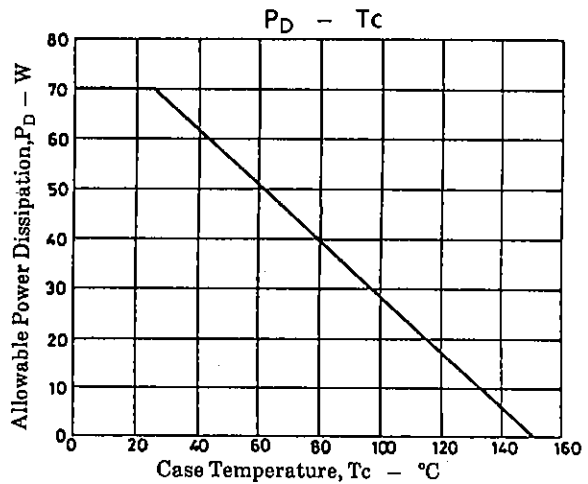
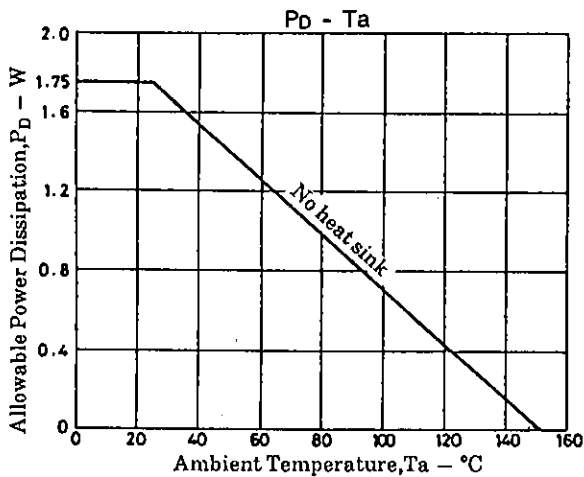
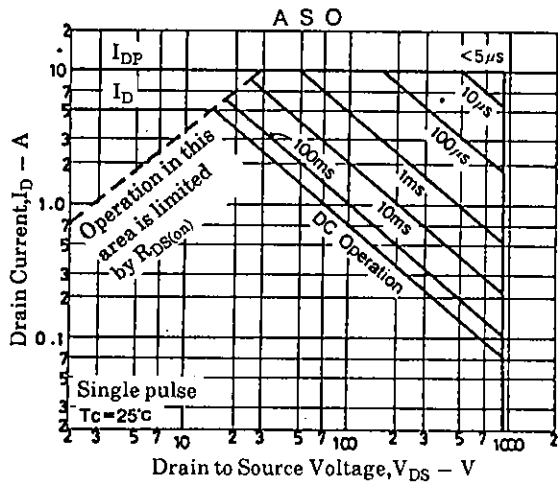
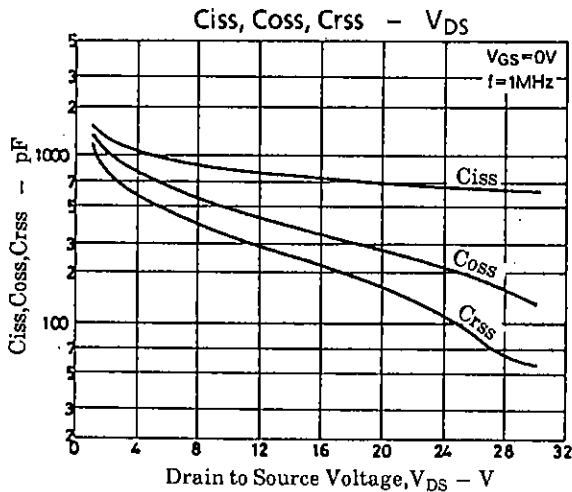
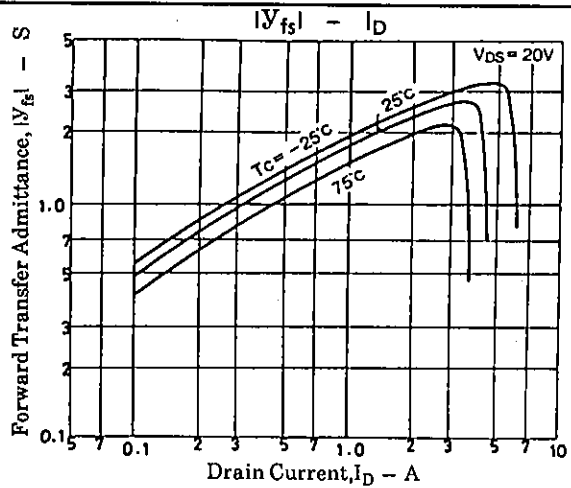
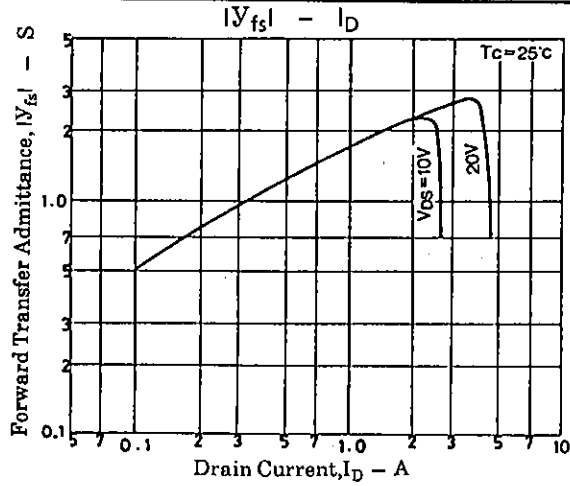
(unit: mm)



**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

6131JN (KOTO) X-6826, 8035 No.3460-1/3





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